1. MOS Capacitor MKT gate 3000 Channel of inversion carrier 32 361/2 767, invesion charse density I'll Qinv = - (ox(Vg-Vt) 至 71室目言 수特 9,55149

달러전압은 어떻게 성강된 결정되는/S 午号 别至却引皇。

Surface potential ØS71 + 7243 depletion 이 되는데, 여 > 208 71 된때부터 충영반전 72 450171 41255ECF (Threshold)

Waep 七 意思的 域则对了, Vo 를 증가나는수록. Surface election of 374 total.

IZUS OPYTHIE Depleting Charge It I P(3) and of Substate of Charge = Qsub = Qdep + Ginv ~ Qdep & \$ + 2TL.

Fermi potential Energy 9 08 = (Ei-Er) bulk

Oles P=NiekT MH P=Na, NA= NiekT = 908= KT In Na OIEL.

Threshold niti 85728 01=3 05=288 - (0x(Vo-Vt) = Qinv 715/EL. でりを 生切 2岁8= 2KT In Na = Øs OIEL.

Vo = Vab + Øs + Vox on14 Vt = 72/2-102

\$ tyl 200 tyl

Vt=Veb+203+Vox OIEL.

Vox = - Qsub = - Qdep nitt Qdep = - 4 Na Wdep Vox = 4NaWaep OILL

Warp= [2Es\$s 0123 Øs = 9NuWdep 2Es PIEL. CEPZYH Vox = JANaZES ØS tyofe Ut = VEB + 2 ØB + J4Nu285020B OIT!

inversion alt 0522083 451

Surface election 5 3801 7129 QSUB = Qdep + Qinv 71 5/2 [L.

Viox = - QSUS = - ( Qdep + QTNV ) OILL.

Vo=Veb+ \$5+Vox 014 95=208010=1

Vg = Veb + 2 dB - Qdep - Qinv

MINH Adep = - 9Na Wdep 0193.

Vo = VIB +2 PR + 9NaWdep - Qinv Cox

Vo = Veb + 20/8 + PNUZESROB - PRINT OPEN VEB + 2 ØB + JANAZES 2 ØB >+ Vt OIE 3

Vo=Vt- Oinv